SN74LVC1G125 Single Bus Buffer Gate With 3-State Output

1 Features

- Available in the Ultra Small 0.64-mm² Package (DPW) With 0.5-mm Pitch
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Provides Down Translation to V_{CC}
- Max t_{pd} of 3.7 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- Cable Modem Termination System
- High-Speed Data Acquisition and Generation
- Military: Radar and Sonar
- Motor Control: High-Voltage
- Power Line Communication Modem
- SSD: Internal or External
- Video Broadcasting and Infrastructure: Scalable Platform
- Video Broadcasting: IP-Based Multi-Format Transcoder
- Video Communications System

4 Simplified Schematic

3 Description

This bus buffer gate is designed for 1.65-V to 5.5-V $V_{\rm CC}$ operation.

The SN74LVC1G125 device is a single line driver with a 3-state output. The output is disabled when the output-enable (OE) input is high.

The CMOS device has high output drive while maintaining low static power dissipation over a broad V_{CC} operating range.

The SN74LVC1G125 device is available in a variety of packages including the ultra-small DPW package with a body size of $0.8 \text{ mm} \times 0.8 \text{ mm}$.

Device Information⁽¹⁾

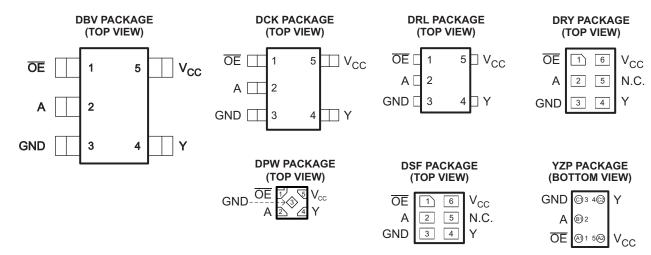
DEVICE NAME	PACKAGE	BODY SIZE (NOM)		
	SOT-23 (5)	2.90 mm × 1.60 mm		
	SC70 (5)	2.00 mm × 1.25 mm		
SN74LVC1G125	SON (6)	1.45 mm × 1.00 mm		
	DSBGA (5)	1.40 mm × 0.90 mm		
	X2SON (4)	0.80 mm × 0.80 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

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•				
Ch	anges from Revision S (April 2014) to Revision T		Р	age
•	Updated Device Information table			1
	Removed PREVIEW status from DPW Pin Out drawing.			
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Ch	anges from Revision R (April 2013) to Revision S		Р	age
•	Added Applications			1
	Added Pin Functions table.			3
	Updated Handling Ratings table			
•	Added Thermal Information table			5
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O.L.	Added Layout section.			
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•	Added Layout section. anges from Revision Q (November 2012) to Revision Added Device Information table. Moved T _{stg} to Handling Ratings table. Added –40°C to 125°C Temperature range to Electrical	R Characterist	P tics.	age 1 4 6
•	Added Layout section. anges from Revision Q (November 2012) to Revision Added Device Information table. Moved T _{stg} to Handling Ratings table.	R Characterist	P tics.	age 1 4 6

6 Pin Configuration and Functions



N.C. – No internal connection
See mechanical drawings for dimensions.

Pin Functions

		PIN								
NAME	DRL, DCK, DBV	DRY, DSF	DPW	YZP	DESCRIPTION					
ŌĒ	1	1	1	A1	Input					
Α	2	2	2	B1	Input					
GND	3	3	3	C1	Ground					
Υ	4	4	4	C2	Output					
V _{CC}	5	6	5	A2	Power pin					
NC	-	5	-	-	Not connected					

7 Specifications

7.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range ⁽²⁾		-0.5	6.5	V
Vo	Voltage range applied to any output in the h	-0.5	6.5	V	
Vo	Voltage range applied to any output in the h	igh or low state (2)(3)	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current		±50	mA	
	Continuous current through V _{CC} or GND			±100	mA

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 Handling Ratings

			MIN	MAX	UNIT
T _{stg}	Storage temperature rang	ne e	-65	150	°C
	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	0	2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	0	1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
	Committee	Operating	1.65	5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
. ,	I limb lavel input valtage	V _{CC} = 2.3 V to 2.7 V	1.7		V
V _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
. ,	Lave lavel inner college	V _{CC} = 2.3 V to 2.7 V		0.7	
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
VI	Input voltage	•	0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
Іон	High-level output current	V 2V		-16	mA
		V _{CC} = 3 V		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V 2V		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δv	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5	
T _A	Operating free-air temperature		-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

7.4 Thermal Information

	nonna miorination									
			SN74LVC1G125							
	THERMAL METRIC ⁽¹⁾	DBV	DCK	DRL	DRY	YZP	DPW	UNIT		
		5 PINS	5 PINS	5 PINS	6 PINS	5 PINS	4 PINS			
$R_{\theta JA}$	Junction-to-ambient thermal resistance	229	278	243	439	130	340			
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	164	93	78	277	54	215			
$R_{\theta JB}$	Junction-to-board thermal resistance	62	65	78	271	51	294	°C/W		
Ψ_{JT}	Junction-to-top characterization parameter	44	2	10	84	1	41	*C/VV		
ψ_{JB}	Junction-to-board characterization parameter	62	64	77	271	50	294			
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	_	_	_	-	_	250			

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

7.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST COMPLETIONS	.,	–40 C to 85 °C	3	−40 C t	o 125 °C	LINUT
PARAMETER	TEST CONDITIONS	V _{cc}	MIN TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾ MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} – 0.1		V _{CC} - 0.1		
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		1.2		
V	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9		V
V _{OH}	$I_{OH} = -16 \text{ mA}$	3 V	2.4		2.4		V
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3		
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8		
	I _{OL} = 100 μA	1.65 V to 5.5 V		0.1		0.1	
	I _{OL} = 4 mA	1.65 V		0.45		0.45	
V	I _{OL} = 8 mA	2.3 V		0.3		0.3	V
V _{OL}	I _{OL} = 16 mA	2.1/		0.4		0.4	V
	I _{OL} = 24 mA	3 V		0.55		0.55	
	I _{OL} = 32 mA	4.5 V		0.55		0.55	
I _I A or OE inputs	V _I = 5.5 V or GND	0 to 5.5 V		±5		±5	μA
I _{off}	V _I or V _O = 5.5 V	0		±10		±10	μΑ
I _{OZ}	V _O = 0 to 5.5 V	3.6 V		10		10	μΑ
I _{CC}	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V		10		10	μΑ
ΔI _{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V		500		500	μΑ
C _I	$V_I = V_{CC}$ or GND	3.3 V	4		4		pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

7.6 Switching Characteristics, $C_L = 15 pF$

over recommended operating free-air temperature range of -40° C to 85° C, $C_L = 15$ pF (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	1.9	6.9	0.7	4.6	0.6	3.7	0.5	3.4	ns

7.7 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range -40° C to 85° C, $C_L = 30$ pF or 50 pF (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
	(INPOT)	(001F01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	2.8	9	1.2	5.5	1	4.5	1	4	ns
t _{en}	ŌĒ	Υ	3.3	10.1	1.5	6.6	1	5.3	1	5	ns
t _{dis}	ŌĒ	Υ	1.3	9.2	1	5	1	5	1	4.2	ns

7.8 Switching Characteristics, -40°C to 125°C

over recommended operating free-air temperature range -40° C to 125°C, $C_L = 30$ pF or 50 pF (unless otherwise noted) (see Figure 4)

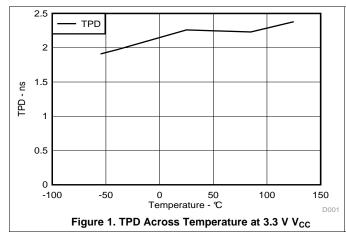
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = 2 ± 0.2		V _{CC} = 0.3		V _{CC} =		UNIT
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	2.8	9.3	1.2	5.8	1	4.7	1	4.2	ns
t _{en}	ŌĒ	Υ	3.3	10.4	1.5	6.9	1	5.6	1	5.2	ns
t _{dis}	ŌĒ	Υ	1.3	9.3	1	5.2	1	5.2	1	4.4	ns

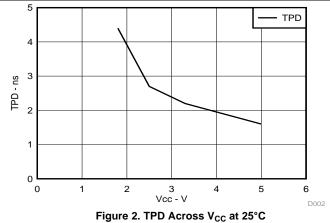
7.9 Operating Characteristics

 $T_A = 25^{\circ}C$

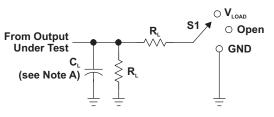
PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	$V_{CC} = 3.3 \text{ V}$	V _{CC} = 5 V	UNIT		
	FARAMETER		CONDITIONS	TYP	TYP	TYP	TYP	ONIT	
_	Power dissipation	Outputs enabled	f 10 MHz	18	18	19	21	pF	
C _{pd}	capacitance	Outputs disabled	f = 10 MHz	2	2	2	4		

7.10 Typical Characteristics





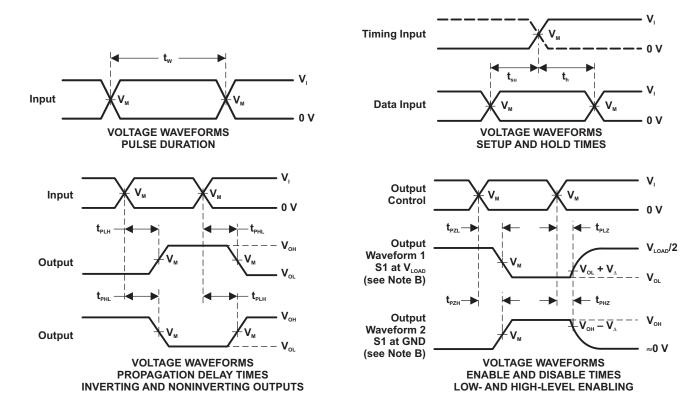
8 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LO	AD	CIE	RCI	UI.	Г
		•		٠.	•

.,	INI	PUTS		.,			.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _∟	R _⊾	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$2.5 \text{ V} \pm 0.2 \text{ V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V

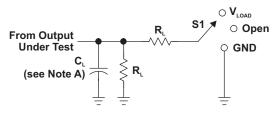


NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

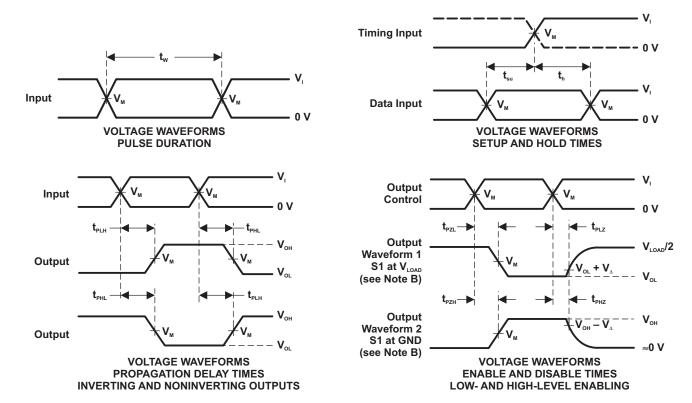
Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INP		.,	.,		•	
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	$R_{\scriptscriptstyle L}$	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \,\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH}^{rzt} and t_{PHL}^{rzn} are the same as t_{pd}^{rd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms

9 Detailed Description

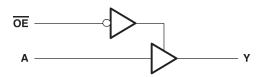
9.1 Overview

The SN74LVC1G125 device contains one buffer gate device with output enable control and performs the Boolean function Y = A. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The DPW package technology is a major breakthrough in IC packaging. Its tiny 0.64 mm square footprint saves significant board space over other package options while still retaining the traditional manufacturing friendly lead pitch of 0.5 mm.

9.2 Functional Block Diagram



9.3 Feature Description

- · Wide operating voltage range
 - Operates from 1.65 V to 5.5 V
- · Allows down voltage translation
- Inputs accept voltages to 5.5 V
- I_{off} feature allows voltages on the inputs and outputs, when V_{CC} is 0 V

9.4 Device Functional Modes

Table 1. Function Table

INP	UTS	OUTPUT
ŌĒ	Α	Υ
L	Н	Н
L	L	L
Н	X	Z

10 Application and Implementation

10.1 Application Information

The SN74LVC1G125 device is a high drive CMOS device that can be used as a output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to $V_{\rm CC}$.

10.2 Typical Application

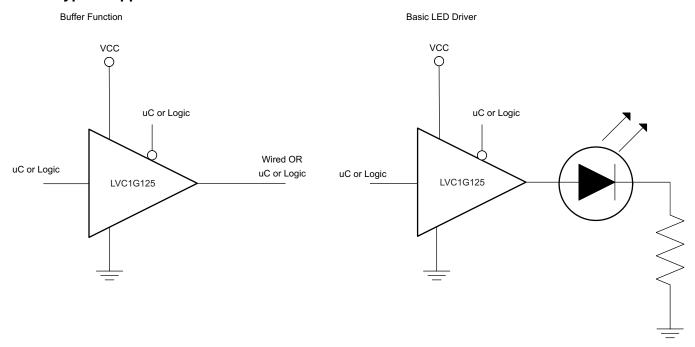


Figure 5. Application Schematic

10.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

10.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

2. Recommend Output Conditions

- Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.
- Outputs should not be pulled above V_{CC}.

Typical Application (continued)

10.2.3 Application Curves

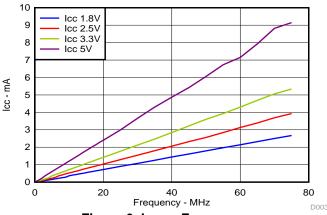


Figure 6. I_{CC} vs Frequency

11 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each VCC pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a 0.1-µF capacitor is recommended and if there are multiple VCC pins then a 0.01-µF or 0.022-µF capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

12 Layout

12.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Figure 7 shows the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or VCC, whichever makes more sense or is more convenient.

12.2 Layout Example



Figure 7. Package Layout

13 Device and Documentation Support

13.1 Trademarks

All trademarks are the property of their respective owners.

13.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC1G125DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C255, C25F, C25J, C25K, C25R, C 25T)	Samples
74LVC1G125DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C255, C25F, C25J, C25K, C25R, C 25T)	Samples
74LVC1G125DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C255, C25F, C25K, C25R)	Samples
74LVC1G125DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM5	Samples
74LVC1G125DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM5	Samples
74LVC1G125DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM5	Samples
74LVC1G125DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM5	Samples
74LVC1G125DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CM7, CMR)	Samples
SN74LVC1G125DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C255, C25F, C25J, C25K, C25R, C 25T)	Samples
SN74LVC1G125DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C255, C25F, C25K, C25R)	Samples
SN74LVC1G125DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 85	(CMF, CMZ)	Samples
SN74LVC1G125DCKJ	ACTIVE	SC70	DCK	5	10000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM5	Samples
SN74LVC1G125DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CM5, CMF, CMJ, CM K, CMR, CMT)	Samples
SN74LVC1G125DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CM5, CMF, CMJ, CM K, CMR, CMT)	Samples
SN74LVC1G125DPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	R4	Samples
SN74LVC1G125DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CM7, CMR)	Samples
SN74LVC1G125DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CM, DM)	Samples

PACKAGE OPTION ADDENDUM

10-Dec-2020

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G125DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CM	Samples
SN74LVC1G125YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(CM7, CMN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

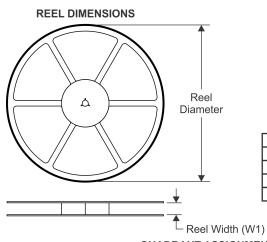
- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G125:

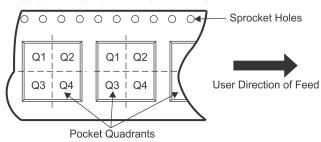
TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



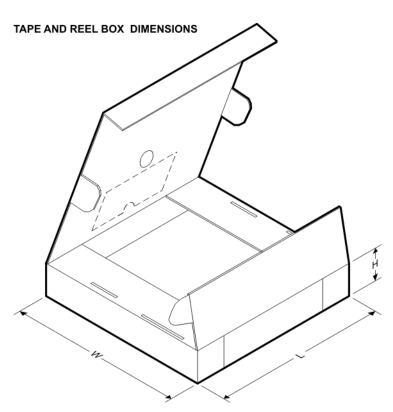
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G125DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
74LVC1G125DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G125DBVT	SOT-23	DBV	5	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G125DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G125DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G125DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G125DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G125DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G125DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G125DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G125DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74LVC1G125DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G125DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G125DRYR	SON	DRY	6	5000	180.0	8.4	1.2	1.65	0.69	4.0	8.0	Q1
SN74LVC1G125DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2

PACKAGE MATERIALS INFORMATION

17-Feb-2021

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G125YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G125DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
74LVC1G125DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LVC1G125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G125DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G125DBVT	SOT-23	DBV	5	250	202.0	201.0	28.0
SN74LVC1G125DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74LVC1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G125DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G125DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G125DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74LVC1G125DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74LVC1G125DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G125DRYR	SON	DRY	6	5000	184.0	184.0	19.0

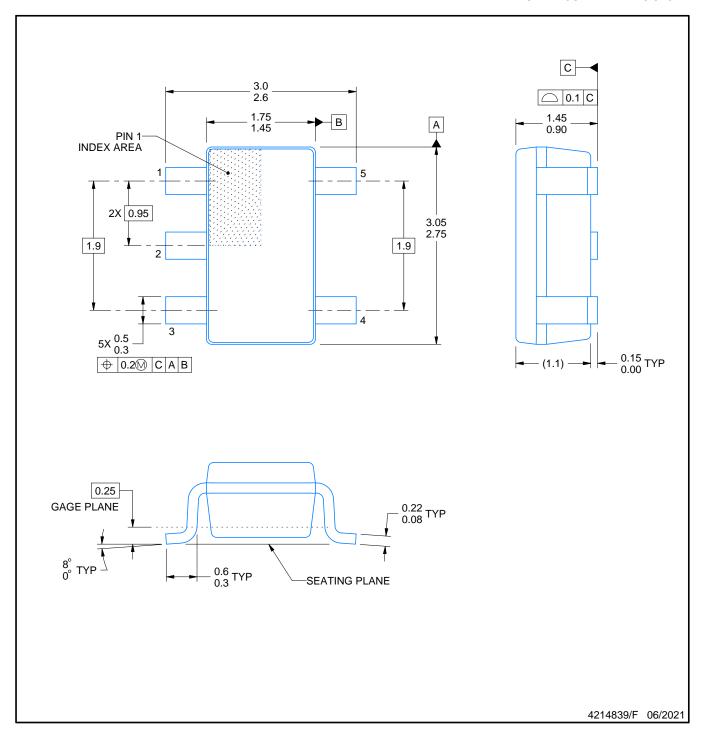
PACKAGE MATERIALS INFORMATION

17-Feb-2021

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G125DRYR	SON	DRY	6	5000	200.0	183.0	25.0
SN74LVC1G125DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G125YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

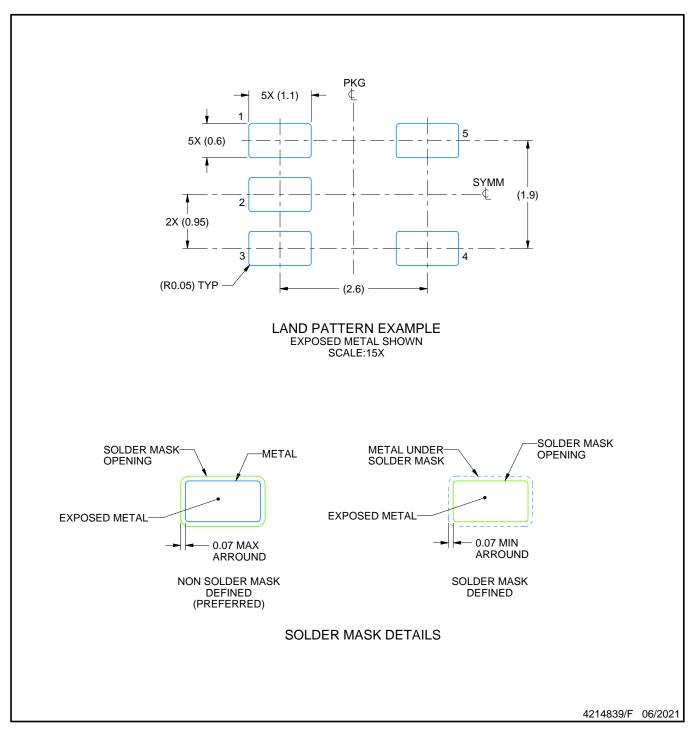
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

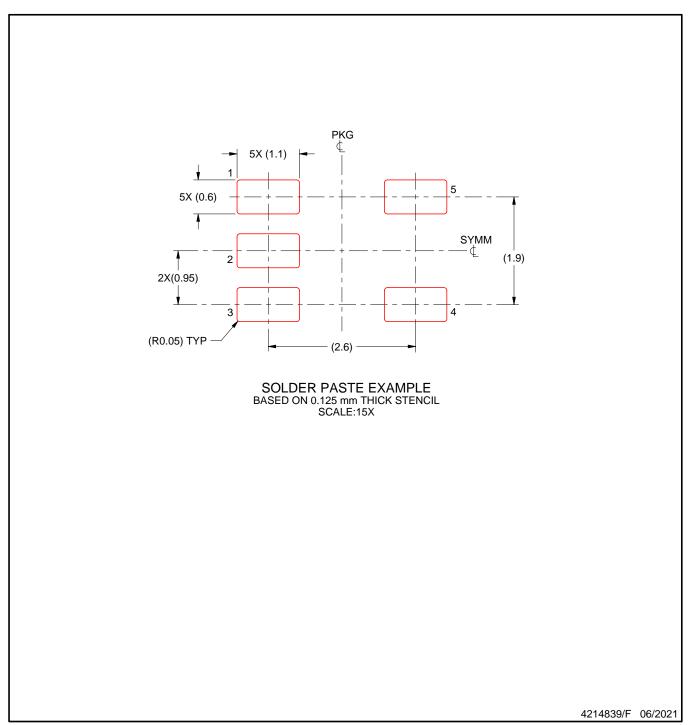
SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



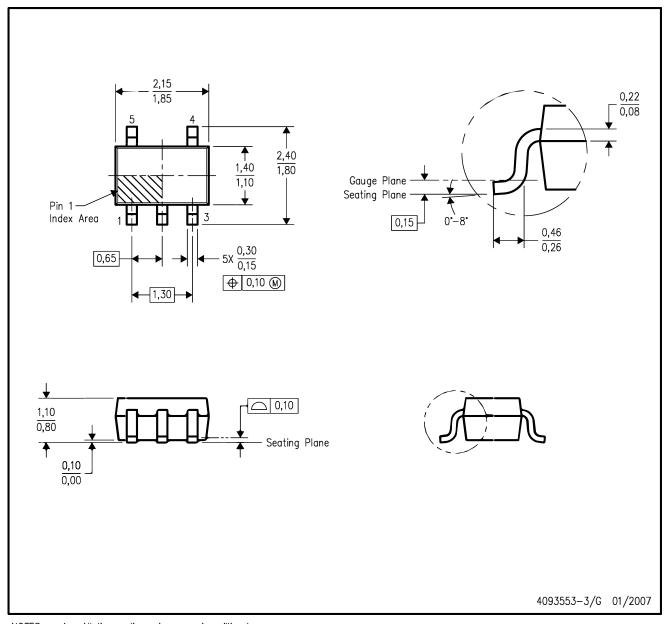
NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

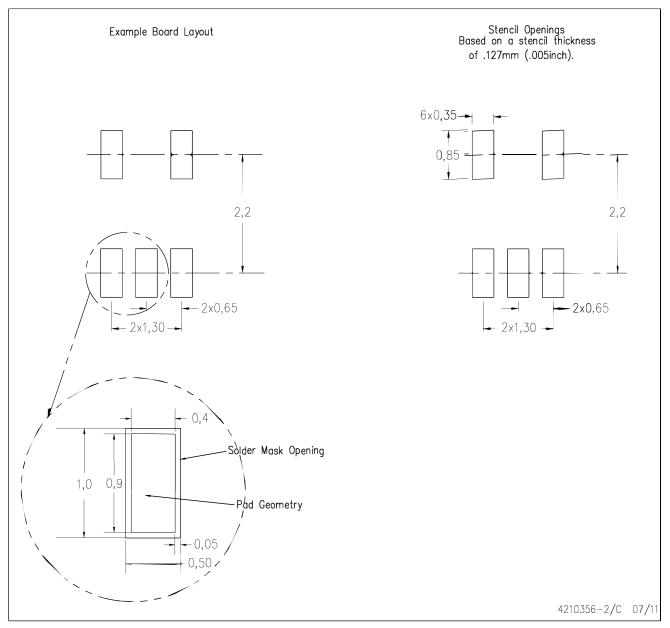


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE

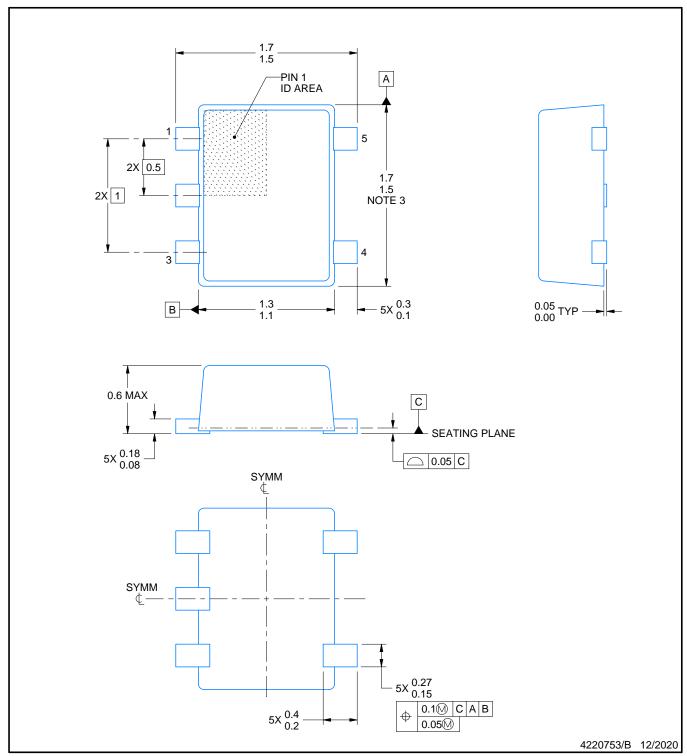


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



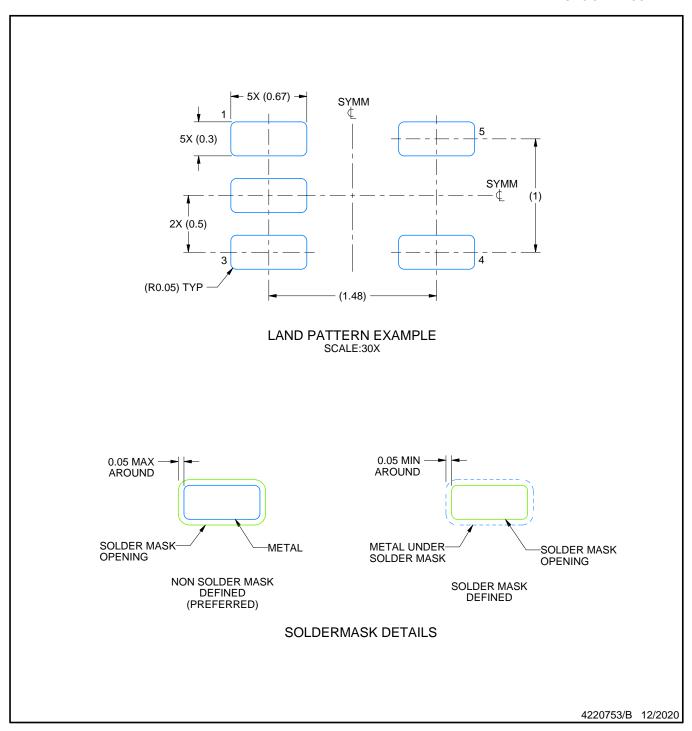
PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1

PLASTIC SMALL OUTLINE

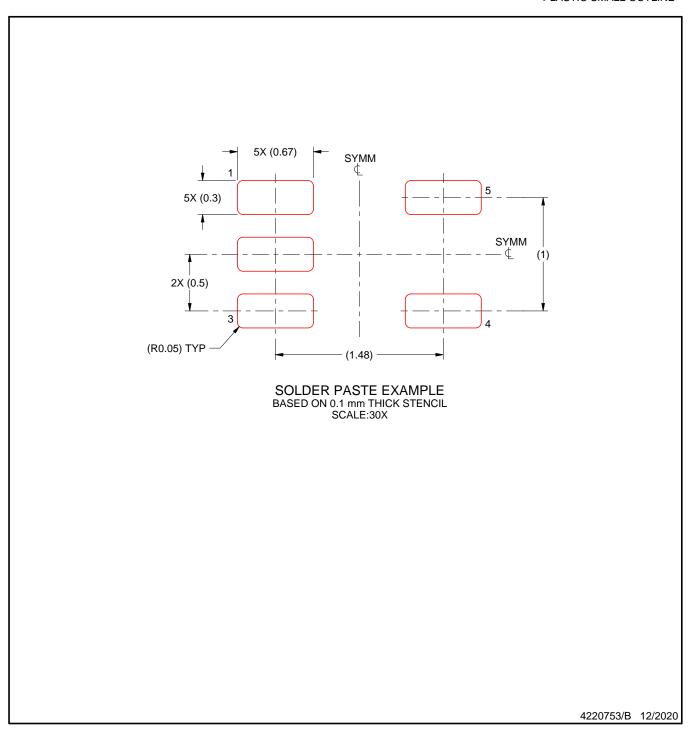


NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

PLASTIC SMALL OUTLINE



NOTES: (continued)

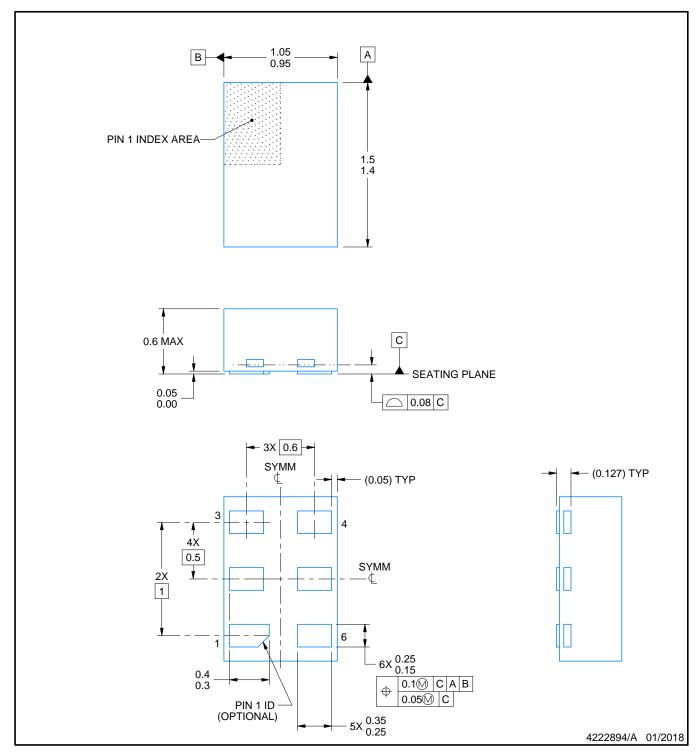
^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

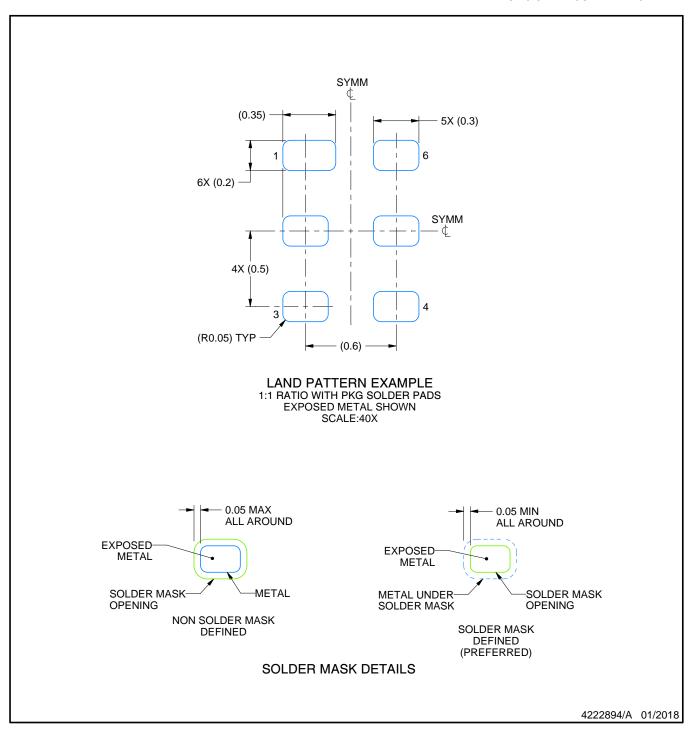




NOTES:

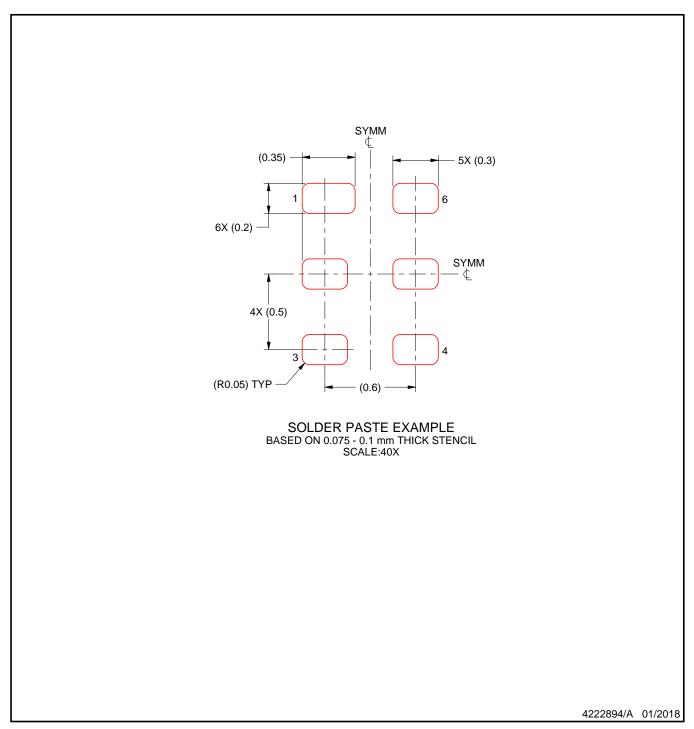
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



NOTES: (continued)

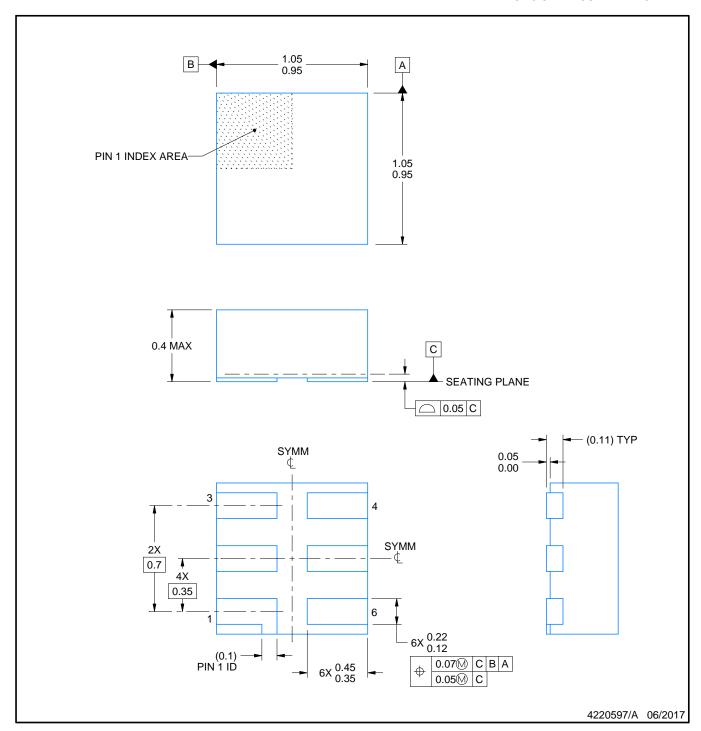
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



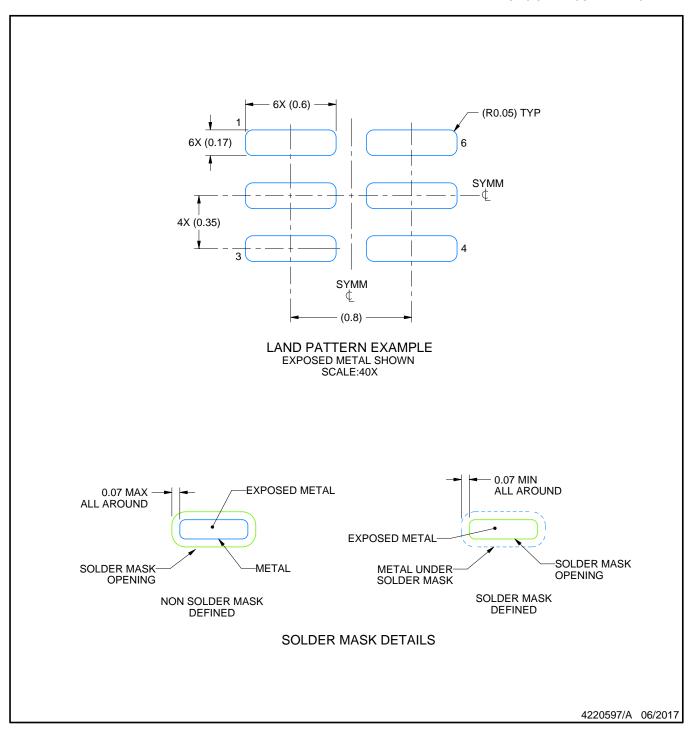


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

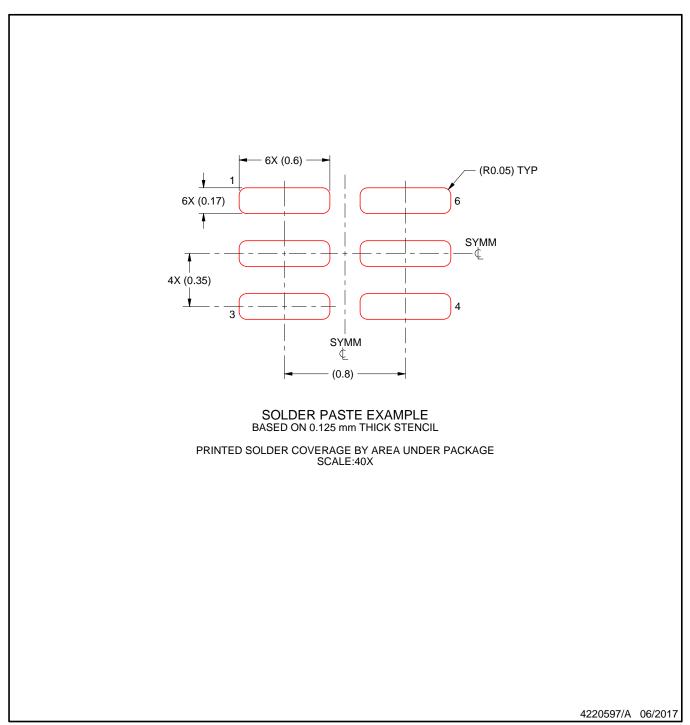
 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.



NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

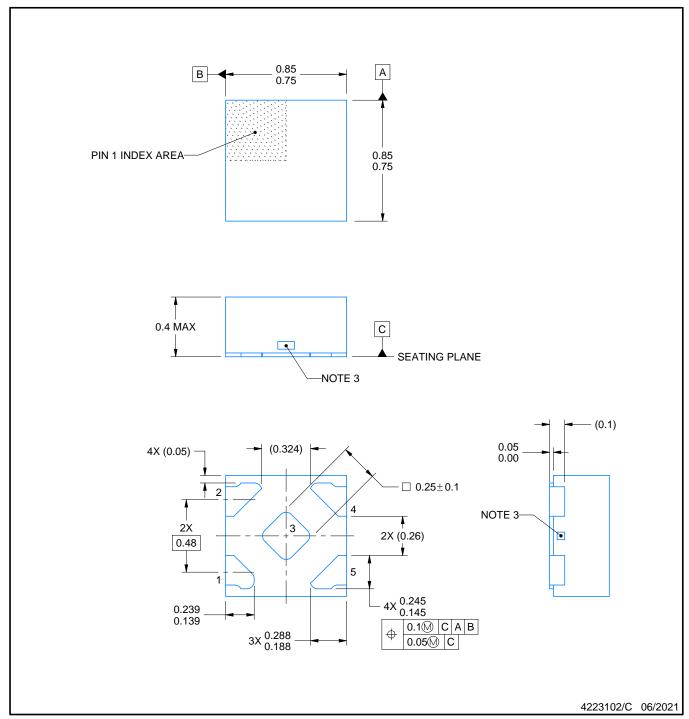


4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

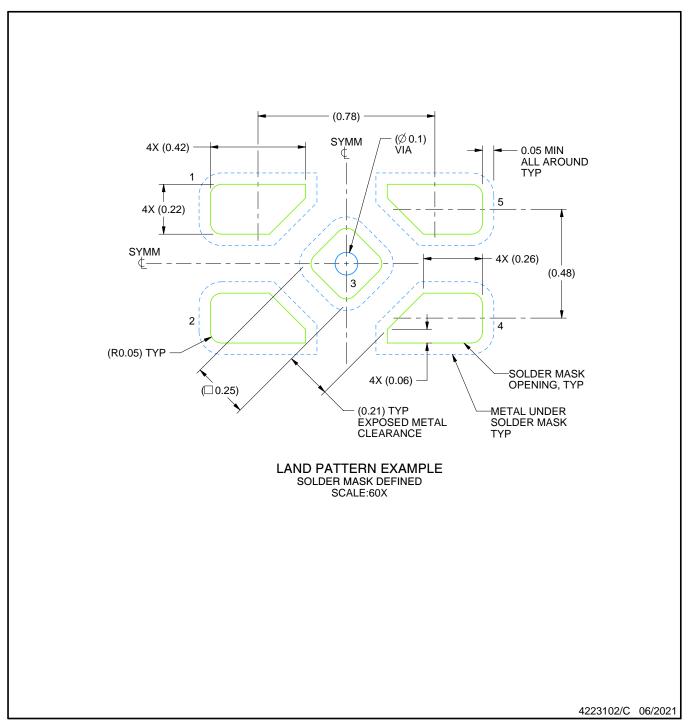




NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.

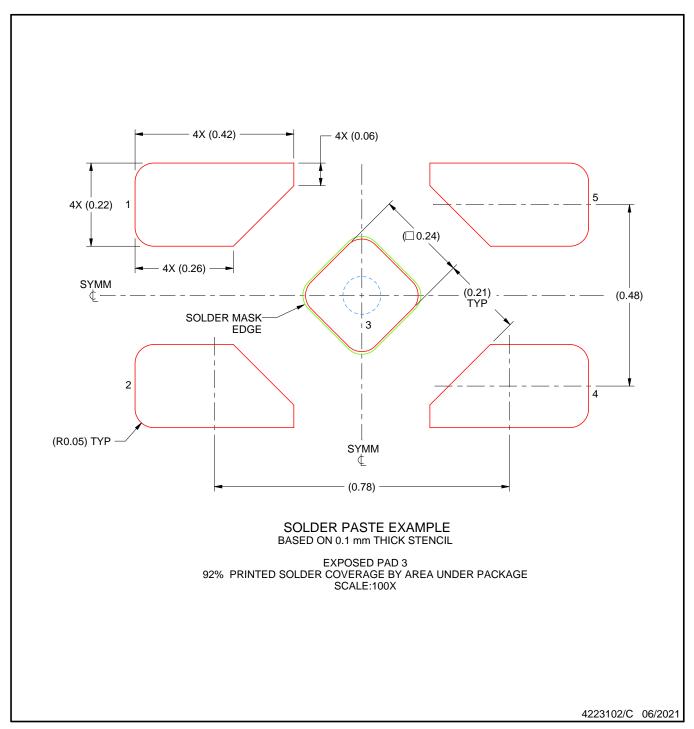




NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).





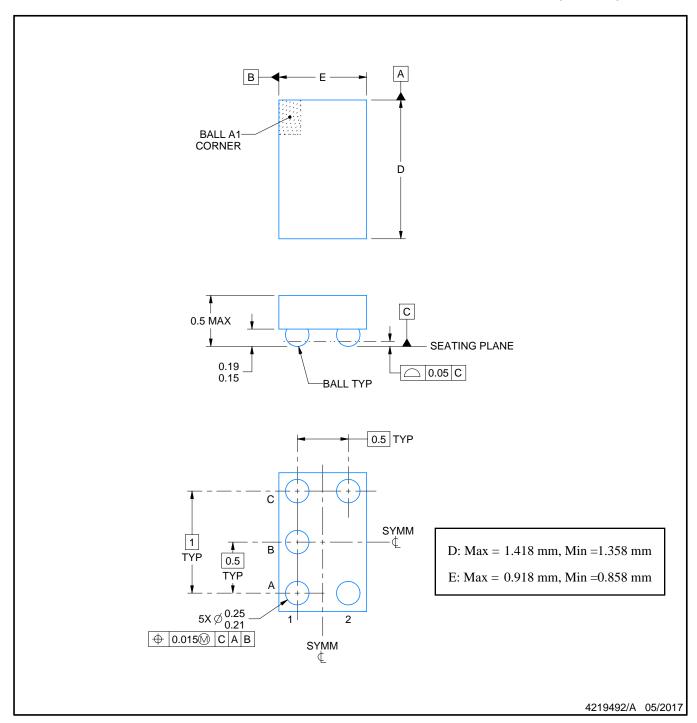
NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





DIE SIZE BALL GRID ARRAY

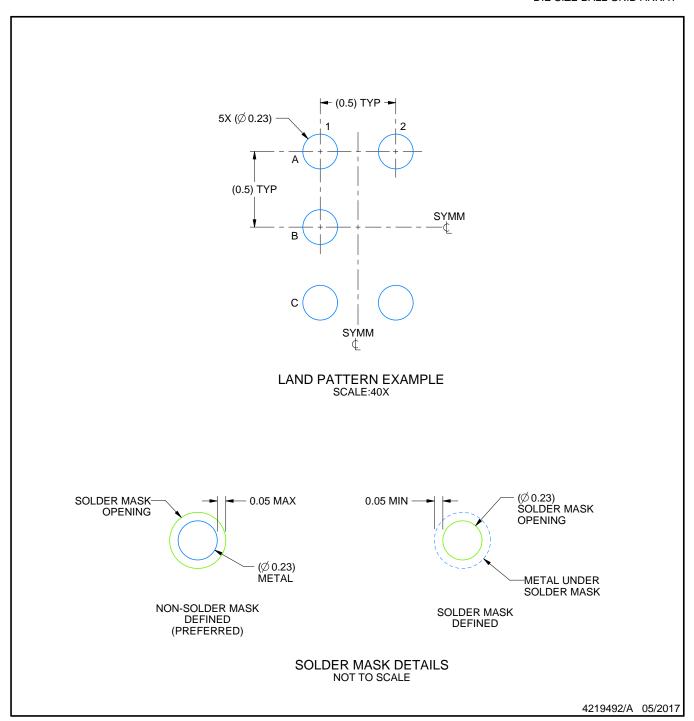


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

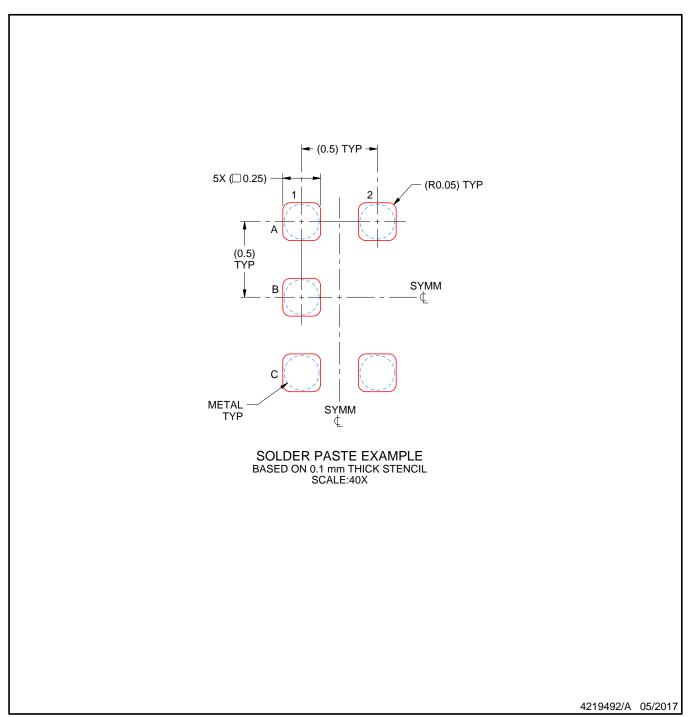


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

